

CS-21,295  
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IN THE SPECIFICATION:

Kindly amend and replace paragraph 16, as follows:

[0016] This surface treatment can be carried out using the magnetron sputtering apparatus shown in the sole drawing in which the apparatus 2 comprises a rotating disk 4 containing a magnet assembly 6 balanced with a countervergent 8. Preferably the magnet component 9 of the magnet assembly 6 is a FeNdB. The rotating disk 4 is secured to the vacuum chamber 10 by electrical insulating blocks 12. Disposed beneath the rotating disk assembly 4-6-8 is a target assembly 14 composed of backplate 16, secured to a target component 18 by ~~viton~~ VITON™ (a DuPont elastomer) 'O' rings 20 and teflon insulator ring 22. The target component 18 has its surface 24 facing into the vacuum chamber 10. The vacuum chamber 10 comprises support plates 26 with a side ~~viton~~ VITON™ vacuum seal 28. A drive motor 30 drives the rotating disk 4 and thus rotates magnet assembly 6. When magnet assembly 6 is energized by a power source (not shown), a rotating sputtering plasma 32 is produced in an inert atmosphere such as argon that can treat the surface 24 of the target component 18. By selecting a desired time and power, as discussed below, to energize the magnet assembly 6, a sputtering plasma 32 will rotate and treat the surface 24 in a novel pattern to provide a uniform, dry surface treatment with minimal material removed. The novel treatment can effectively reduce the  $R_a$  uniformity of the surface of a wafer by at least 10% and less than  $R_a$  uniformity 1.6%.